Complementary Silicon Power Transistors

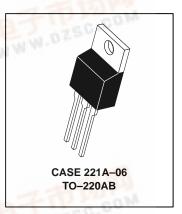
These complementary silicon power transistors are designed for high—speed switching applications, such as switching regulators and high frequency inverters. The devices are also well—suited for drivers for high power switching circuits.

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- Fast Switching t_f = 90 ns (Max)
- Key Parameters Specified @ 100°C
- Low Collector–Emitter Saturation Voltage VCE(sat) = 1.0 V (Max) @ 8.0 A
- Complementary Pairs Simplify Circuit Designs



15 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
80 VOLTS
83 WATTS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	80	Vdc
Collector–Emitter Voltage	VCEV	100	Vdc
Emitter Base Voltage	V _{EB}	7.0	Vdc
Collector Current — Continuous — Peak (1)	I _C	15 20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	83 0.67	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction to Case	R _θ JC	1.5	°C/W	
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	62.5	°C/W	
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C	

(1) Pulse Width ≤ 6.0 ms, Duty Cycle ≤ 50%.

NOTE: All polarities are shown for NPN transistors. For PNP transistors, reverse polarities.





D44VH D45VH

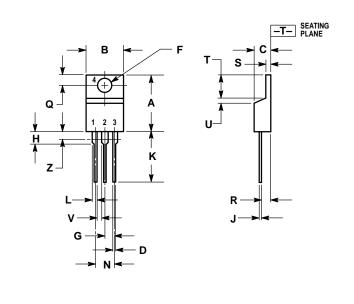
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTIC	cs						
Collector–Emitter Sust (I _C = 25 mAdc, I _B =	0 0 v /		VCEO(sus)	80	_	_	Vdc
	off Current /, VBE(off) = 4.0 Vdc) /, VBE(off) = 4.0 Vdc, T _C = 100°C))	ICEV	_ _ _	_ _	10 100	μAdc
Emitter Base Cutoff Cu (V _{EB} = 7.0 Vdc, I _C =			IEBO	_	_	10	μAdc
ON CHARACTERISTIC	S (1)						
DC Current Gain (I _C = 2.0 Adc, V _{CE} : (I _C = 4.0 Adc, V _{CE} :			h _{FE}	35 20	_ _	_ _	_
Collector–Emitter Satu (I _C = 8.0 Adc, I _B = 0 (I _C = 15 Adc, I _B = 3	0.4 Adc) 0.8 Adc)	D44VH10 D45VH10 D44VH10 D45VH10	VCE(sat)	1 1 1 1		0.4 1.0 0.8 1.5	Vdc
	0.4 Adc)	D44VH10 D45VH10 D44VH10 D45VH10	VBE(sat)	- - - -	_ _ _	1.2 1.0 1.1 1.5	Vdc
DYNAMIC CHARACTE	RISTICS						
Current Gain Bandwid (I _C = 0.1 Adc, V _{CE} :	th Product = 10 Vdc, f = 20 MHz)		fT	_	50	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _C = 0, f _{test} = 1.0 MHz) D44VH10 D45VH10		C _{ob}		120 275		pF	
SWITCHING CHARACT	ERISTICS						
Delay Time			td		_	50	ns
Rise Time	(VCC = 20 Vdc, 1C = 6.0 Adc,		t _r		_	250	
Storage Time	$I_{B1} = I_{B2} = 0.8 \text{ A}$	idc)	t _S	_	_	700	
Fall Time			t _f	_	_	90	

⁽¹⁾ Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2\%$.

Maria Diala Dan Taraka Dan Dan

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**

D44VH D45VH

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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

